ABSTRACT OF THE DISCLOSURE

A method of manufacturing an electron device provided with minute structure such as a semiconductor integrated circuit using projection exposure technique and phase shift mask technique, maintaining a high yield is disclosed. In an electron device manufacturing method according to the invention, a desired electron device is manufactured by printing a light shielding film pattern on a photosensitive film provided on the surface of a workpiece by a projection tool using a mask where a phase shifter having predetermined thickness is partially formed on the flat surface of a transparent plate and a light shielding film having a predetermined pattern and made of non-metal is partially provided with the film covering the end of the shifter and developing the photosensitive film. Further, concretely, the above pattern is printed using a mask where the light shielding film made of non-metal is partially extended on the surface of the shifter and the transparent plate including the end of the shifter by the projection tool. According to the electron device manufacturing method according to the invention, an electron device provided with minute structure can be precisely manufactured maintaining a high yield.